

# 2SC5890

Silicon NPN Epitaxial  
UHF / VHF wide band amplifier

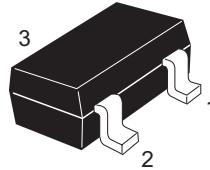
REJ03G0763-0100  
(Previous ADE-208-1533)  
Rev.1.00  
Aug.10.2005

## Features

- High gain bandwidth product:  
 $f_T = 7.8$  GHz typ.
- High power gain and low noise figure;  
PG = 12 dB typ., NF = 1.0 dB typ. at  $f = 900$  MHz
- High collector power dissipation:  
 $P_C = 700$  mW when using alumina ceramic board (25 x 60 x 0.7 mm)
- High withstanding to ESD of collector to emitter:  
Withstand up to 700 V (only real value) at  $C = 200$  pF,  $R_s = 0$  condition.

## Outline

RENESAS Package code: PLSP0003ZB-A  
(Package name: MPAK)



1. Emitter
2. Base
3. Collector

Note: Marking is "FS-".

## Absolute Maximum Ratings

( $T_a = 25^\circ\text{C}$ )

Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	20	V
Collector to emitter voltage	$V_{CEO}$	12	V
Emitter to base voltage	$V_{EBO}$	1.5	V
Collector current	$I_C$	75	mA
Collector power dissipation	$P_C$	700*	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

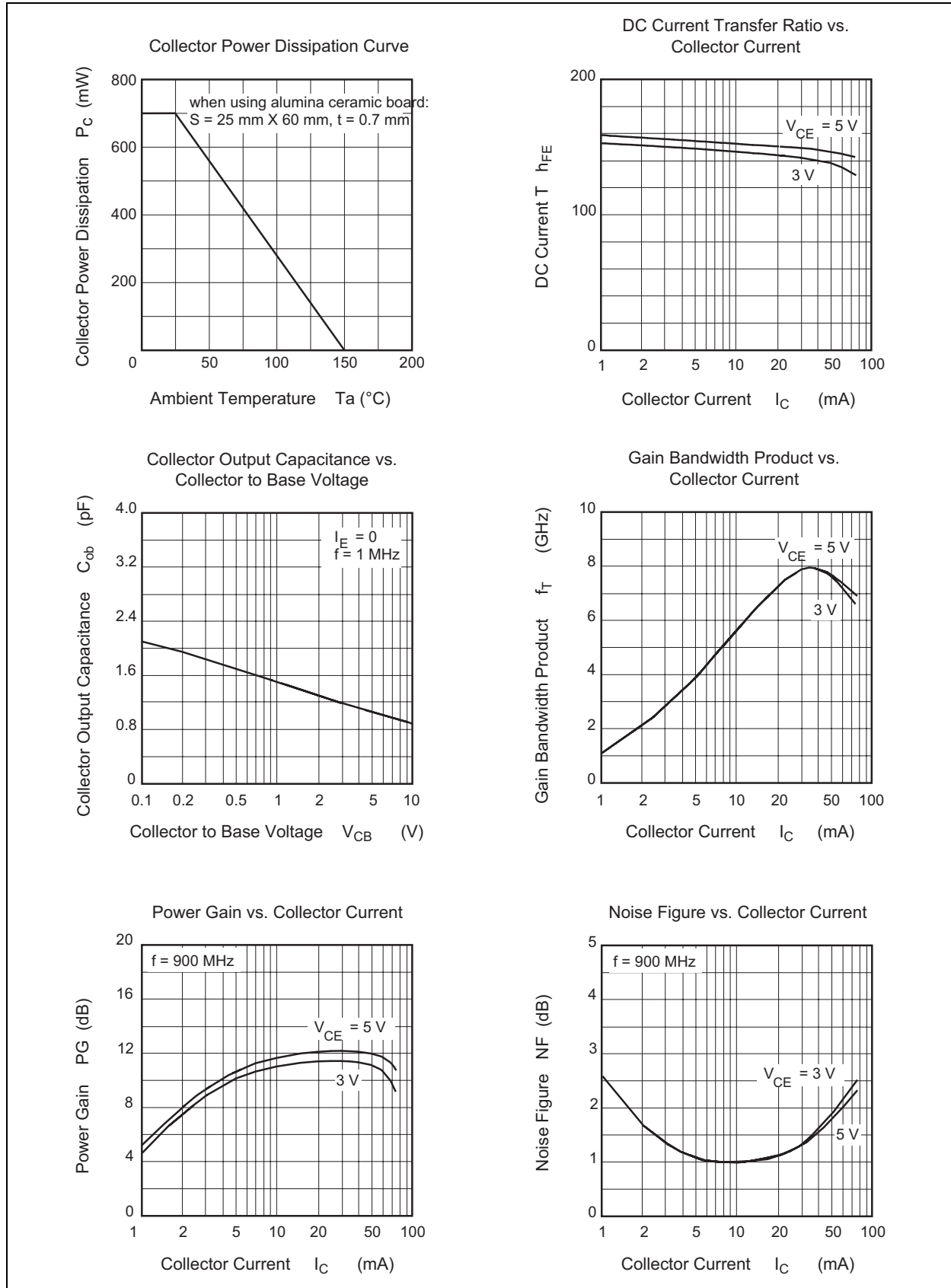
\*When using alumina ceramic board (25 x 60 x 0.7 mm)

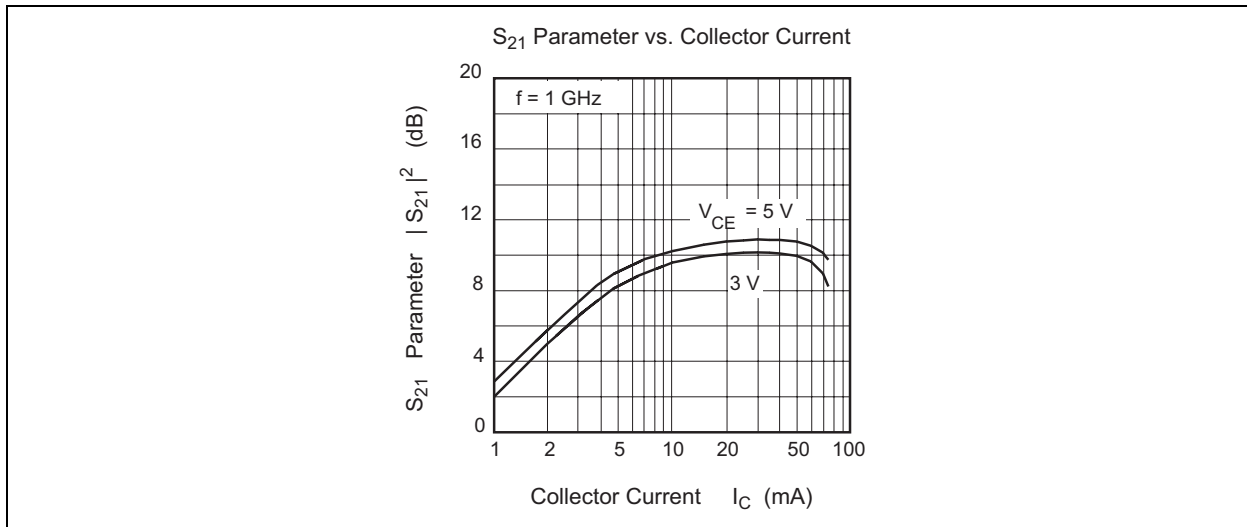
## Electrical Characteristics

(T<sub>a</sub> = 25°C)

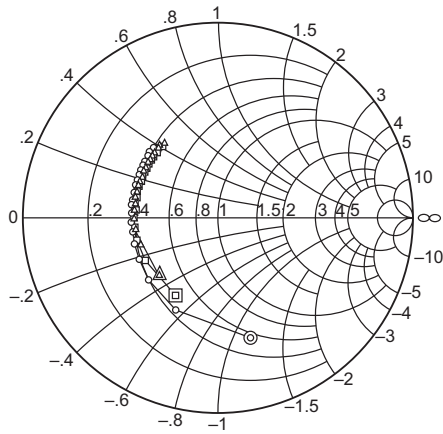
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	20	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector cutoff current	$I_{CBO}$	—	—	1	$\mu A$	$V_{CB} = 12 V, I_E = 0$
Collector cutoff current	$I_{CEO}$	—	—	1	mA	$V_{CE} = 9 V, R_{BE} = \infty$
Emitter cutoff current	$I_{EBO}$	—	—	10	$\mu A$	$V_{EB} = 1.5 V, I_C = 0$
DC current transfer ratio	$h_{FE}$	100	150	200		$V_{CE} = 5 V, I_C = 20 mA$
Collector output capacitance	$C_{ob}$	—	0.9	1.5	pF	$V_{CB} = 5 V, I_E = 0, f = 1 MHz$
Reverse transfer capacitance	$C_{re}$	—	0.85	—	pF	$V_{CB} = 5 V, I_E = 0, f = 1 MHz$
Gain bandwidth product	$f_T$	5.5	7.8	—	GHz	$V_{CE} = 5 V, I_C = 30 mA, f = 1 GHz$
Forward transfer coefficient	$ S_{21} ^2$	—	11	—	dB	$V_{CE} = 5 V, I_C = 30 mA, f = 1 GHz$
Power gain	PG	9.5	12	—	dB	$V_{CE} = 5 V, I_C = 30 mA, f = 900 MHz$
Noise figure	NF	—	1.0	1.9	dB	$V_{CE} = 5 V, I_C = 5 mA, f = 900 MHz$

Main Characteristics



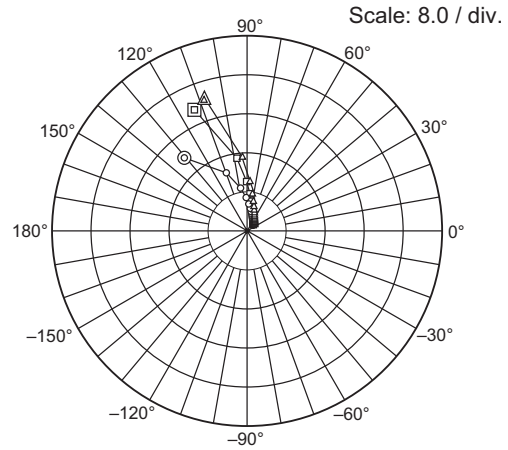


S11 Parameter vs. Frequency



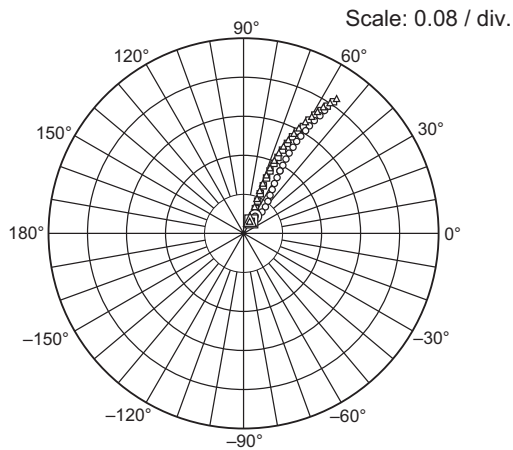
Condition:  $V_{CE} = 3\text{ V}$ ,  $Z_O = 50\ \Omega$   
 100 to 2000 MHz (100 MHz Step)  
 ○—○ ( $I_C = 10\text{ mA}$ )  
 □—□ ( $I_C = 30\text{ mA}$ )  
 ▲—▲ ( $I_C = 50\text{ mA}$ )

S21 Parameter vs. Frequency



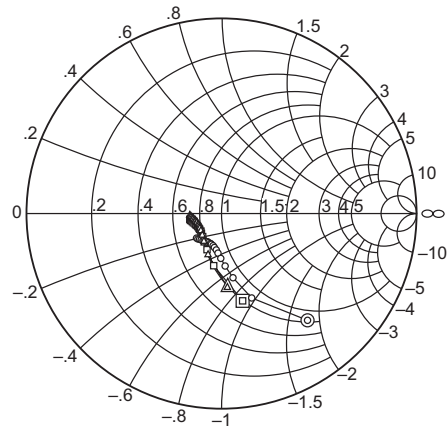
Condition:  $V_{CE} = 3\text{ V}$ ,  $Z_O = 50\ \Omega$   
 100 to 2000 MHz (100 MHz Step)  
 ○—○ ( $I_C = 10\text{ mA}$ )  
 □—□ ( $I_C = 30\text{ mA}$ )  
 ▲—▲ ( $I_C = 50\text{ mA}$ )

S12 Parameter vs. Frequency



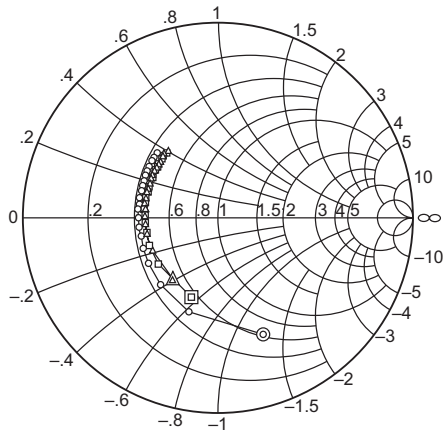
Condition:  $V_{CE} = 3\text{ V}$ ,  $Z_O = 50\ \Omega$   
 100 to 2000 MHz (100 MHz Step)  
 ○—○ ( $I_C = 10\text{ mA}$ )  
 □—□ ( $I_C = 30\text{ mA}$ )  
 ▲—▲ ( $I_C = 50\text{ mA}$ )

S22 Parameter vs. Frequency



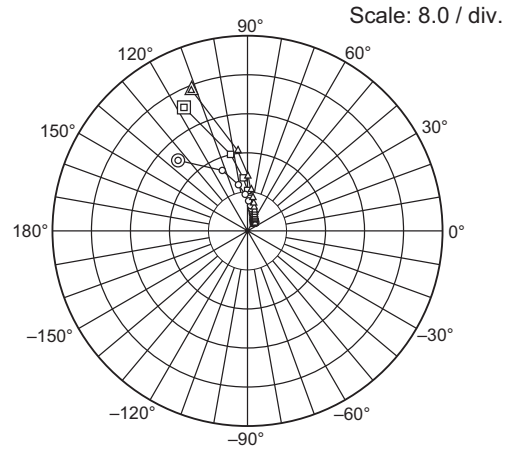
Condition:  $V_{CE} = 3\text{ V}$ ,  $Z_O = 50\ \Omega$   
 100 to 2000 MHz (100 MHz Step)  
 ○—○ ( $I_C = 10\text{ mA}$ )  
 □—□ ( $I_C = 30\text{ mA}$ )  
 ▲—▲ ( $I_C = 50\text{ mA}$ )

S11 Parameter vs. Frequency



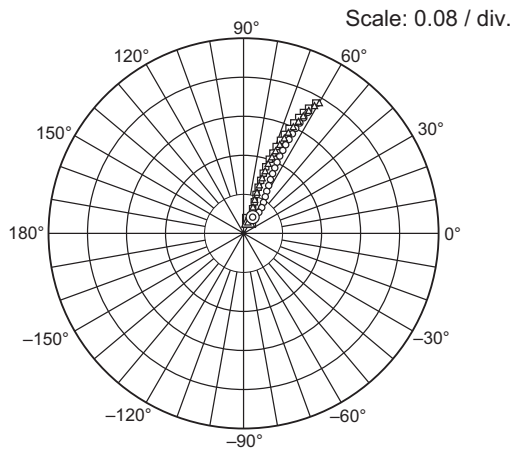
Condition:  $V_{CE} = 5\text{ V}$ ,  $Z_O = 50\ \Omega$   
 100 to 2000 MHz (100 MHz Step)  
 ○ (IC = 10 mA)  
 □ (IC = 30 mA)  
 ▲ (IC = 50 mA)

S21 Parameter vs. Frequency



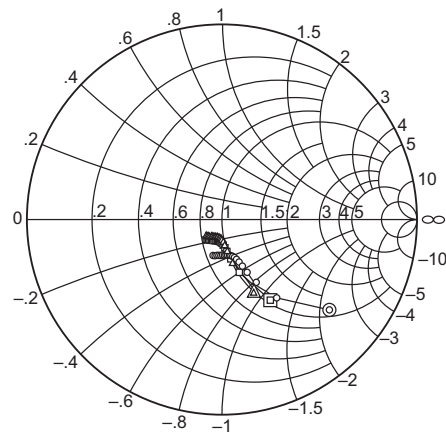
Condition:  $V_{CE} = 5\text{ V}$ ,  $Z_O = 50\ \Omega$   
 100 to 2000 MHz (100 MHz Step)  
 ○ (IC = 10 mA)  
 □ (IC = 30 mA)  
 ▲ (IC = 50 mA)

S12 Parameter vs. Frequency



Condition:  $V_{CE} = 5\text{ V}$ ,  $Z_O = 50\ \Omega$   
 100 to 2000 MHz (100 MHz Step)  
 ○ (IC = 10 mA)  
 □ (IC = 30 mA)  
 ▲ (IC = 50 mA)

S22 Parameter vs. Frequency



Condition:  $V_{CE} = 5\text{ V}$ ,  $Z_O = 50\ \Omega$   
 100 to 2000 MHz (100 MHz Step)  
 ○ (IC = 10 mA)  
 □ (IC = 30 mA)  
 ▲ (IC = 50 mA)

## Sparameter

 $(V_{CE} = 3V, I_C = 10mA, Z_o = 50\Omega)$ 

f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.635	-75.2	19.73	130.5	0.042	55.9	0.698	-51.2
200	0.524	-115.1	12.64	109.7	0.058	49.5	0.455	-70.6
300	0.483	-138.4	8.86	98.7	0.071	50.6	0.330	-80.4
400	0.462	-152.3	6.82	91.6	0.083	52.8	0.266	-86.8
500	0.454	-162.6	5.51	86.4	0.096	55.2	0.226	-91.9
600	0.448	-170.5	4.63	81.9	0.108	56.8	0.201	-96.3
700	0.451	-176.9	4.01	78.0	0.121	58.2	0.185	-99.5
800	0.448	177.1	3.54	74.2	0.134	59.0	0.175	-103.3
900	0.453	171.7	3.17	71.5	0.149	59.8	0.169	-106.3
1000	0.452	168.6	2.87	68.2	0.162	60.0	0.163	-109.9
1100	0.453	163.6	2.63	65.1	0.176	60.3	0.161	-112.3
1200	0.459	158.8	2.43	62.5	0.190	60.4	0.162	-116.0
1300	0.460	155.4	2.27	59.8	0.204	60.1	0.160	-118.1
1400	0.464	151.8	2.13	57.4	0.218	60.0	0.162	-121.1
1500	0.469	148.8	2.00	54.8	0.232	59.5	0.162	-124.7
1600	0.474	145.5	1.89	52.2	0.246	58.8	0.167	-126.3
1700	0.477	143.0	1.80	49.9	0.260	58.6	0.169	-129.4
1800	0.482	139.0	1.72	47.9	0.274	57.9	0.172	-132.4
1900	0.491	136.7	1.65	45.6	0.288	57.1	0.177	-134.6
2000	0.490	133.2	1.59	43.5	0.302	56.6	0.179	-137.2

f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.449	-118.4	27.19	113.3	0.029	57.1	0.459	-76.8
200	0.431	-150.0	15.04	98.0	0.043	61.4	0.270	-98.5
300	0.429	-165.1	10.09	90.5	0.060	65.3	0.199	-112.0
400	0.428	-174.1	7.63	85.6	0.076	67.0	0.170	-121.5
500	0.430	179.3	6.12	81.7	0.093	67.6	0.152	-129.4
600	0.421	174.0	5.12	78.2	0.110	67.9	0.144	-135.4
700	0.431	169.6	4.42	75.3	0.126	67.8	0.139	-139.6
800	0.428	165.6	3.89	72.2	0.143	67.4	0.138	-144.1
900	0.438	161.3	3.48	69.8	0.160	66.9	0.137	-146.7
1000	0.436	157.8	3.15	66.9	0.176	65.9	0.138	-150.7
1100	0.436	154.0	2.88	64.2	0.193	65.3	0.138	-152.5
1200	0.445	150.5	2.66	62.3	0.209	64.3	0.142	-155.5
1300	0.446	147.5	2.49	59.7	0.225	63.4	0.141	-157.2
1400	0.446	144.6	2.33	57.5	0.240	62.5	0.146	-159.1
1500	0.451	141.6	2.19	55.0	0.256	61.2	0.148	-162.0
1600	0.454	138.6	2.07	53.0	0.272	60.2	0.151	-162.2
1700	0.457	136.2	1.98	50.6	0.287	59.3	0.155	-164.6
1800	0.459	132.6	1.88	49.0	0.301	58.2	0.158	-166.8
1900	0.473	130.7	1.80	46.6	0.317	57.0	0.163	-167.7
2000	0.465	127.4	1.73	44.9	0.331	55.9	0.165	-169.7



$(V_{CE} = 3V, I_C = 50mA, Z_o = 50\Omega)$ 

f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.424	-136.3	28.25	108.0	0.025	60.4	0.382	-86.3
200	0.426	-160.8	15.12	94.5	0.041	65.8	0.225	-108.8
300	0.433	-171.8	10.08	88.0	0.058	69.0	0.172	-122.9
400	0.437	-179.2	7.59	83.5	0.076	70.1	0.152	-132.5
500	0.440	175.1	6.09	80.1	0.093	70.2	0.141	-140.5
600	0.435	170.8	5.08	76.8	0.110	69.9	0.138	-146.0
700	0.443	166.5	4.39	73.9	0.128	69.4	0.134	-149.8
800	0.441	162.8	3.86	70.9	0.145	68.6	0.135	-153.3
900	0.446	158.4	3.44	68.4	0.163	67.8	0.136	-155.4
1000	0.447	155.7	3.11	65.9	0.179	66.8	0.138	-159.5
1100	0.444	152.5	2.86	63.3	0.196	65.9	0.138	-160.9
1200	0.455	148.4	2.64	61.0	0.212	64.8	0.143	-163.1
1300	0.455	145.9	2.47	58.5	0.229	63.6	0.142	-164.6
1400	0.463	142.3	2.31	56.5	0.244	62.7	0.147	-166.3
1500	0.462	140.1	2.17	54.0	0.261	61.3	0.151	-169.0
1600	0.466	137.4	2.05	51.9	0.276	60.3	0.153	-169.0
1700	0.469	135.1	1.97	50.0	0.291	59.1	0.157	-171.3
1800	0.474	131.2	1.87	48.3	0.306	58.0	0.161	-173.0
1900	0.481	129.6	1.79	46.0	0.321	56.7	0.165	-173.5
2000	0.476	126.4	1.72	44.0	0.336	55.6	0.166	-176.0

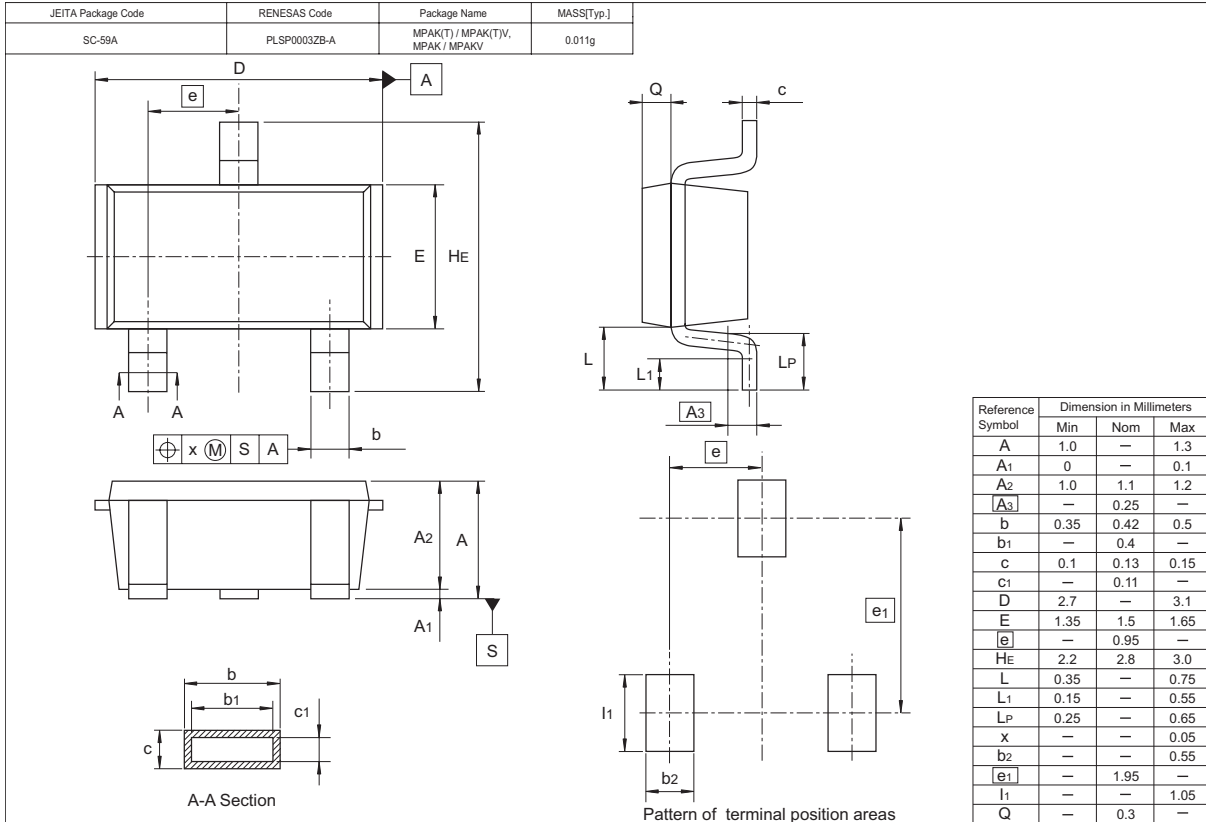
f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.643	-69.1	20.28	134.6	0.038	60.7	0.719	-40.0
200	0.512	-107.8	13.36	113.9	0.053	54.0	0.485	-55.1
300	0.460	-130.9	9.51	102.7	0.064	54.8	0.362	-61.6
400	0.433	-146.9	7.33	95.6	0.075	57.2	0.295	-64.8
500	0.421	-157.7	5.96	90.2	0.087	59.4	0.256	-66.7
600	0.411	-166.4	5.01	85.6	0.098	61.2	0.230	-68.5
700	0.414	-173.0	4.34	81.7	0.111	62.2	0.212	-70.4
800	0.414	-179.6	3.83	78.0	0.123	63.5	0.200	-72.5
900	0.419	174.3	3.43	75.0	0.136	64.1	0.192	-74.5
1000	0.414	170.8	3.10	71.8	0.149	64.5	0.186	-76.9
1100	0.421	166.3	2.84	68.8	0.161	64.8	0.182	-78.9
1200	0.420	161.3	2.63	66.0	0.175	64.9	0.180	-81.9
1300	0.424	157.6	2.45	63.3	0.188	64.7	0.178	-84.6
1400	0.428	154.2	2.29	61.2	0.201	64.6	0.179	-87.2
1500	0.435	150.5	2.16	58.4	0.214	64.2	0.178	-90.2
1600	0.439	147.4	2.03	56.0	0.227	63.9	0.180	-93.1
1700	0.444	144.2	1.94	53.8	0.240	63.6	0.181	-96.2
1800	0.450	140.1	1.85	51.5	0.254	63.0	0.182	-99.2
1900	0.454	137.5	1.77	49.4	0.267	62.5	0.185	-102.2
2000	0.458	134.0	1.69	47.3	0.281	62.0	0.187	-105.3

$(V_{CE} = 5V, I_C = 30mA, Z_o = 50\Omega)$ 

f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.430	-108.9	28.25	118.1	0.026	61.8	0.482	-59.0
200	0.387	-142.7	16.05	102.5	0.040	65.5	0.283	-72.0
300	0.380	-158.5	10.90	94.7	0.055	69.2	0.205	-77.8
400	0.374	-168.7	8.27	89.8	0.070	70.7	0.165	-81.7
500	0.375	-176.5	6.67	85.8	0.085	71.8	0.143	-84.6
600	0.376	177.6	5.59	82.3	0.101	72.1	0.130	-87.9
700	0.384	172.9	4.82	79.4	0.116	71.7	0.121	-90.6
800	0.383	167.8	4.24	76.5	0.131	71.6	0.116	-93.5
900	0.388	164.0	3.78	73.8	0.147	71.3	0.112	-96.9
1000	0.385	159.5	3.43	70.9	0.162	70.6	0.111	-99.9
1100	0.390	155.7	3.13	68.4	0.177	69.7	0.111	-102.7
1200	0.398	152.4	2.90	66.2	0.192	69.2	0.111	-106.2
1300	0.396	148.1	2.70	63.8	0.207	68.2	0.112	-108.8
1400	0.406	146.2	2.53	61.7	0.221	67.4	0.114	-111.8
1500	0.407	142.5	2.37	59.2	0.236	66.4	0.115	-115.0
1600	0.408	139.8	2.25	57.1	0.250	65.4	0.118	-117.5
1700	0.414	137.8	2.13	54.9	0.265	64.4	0.122	-120.7
1800	0.420	133.6	2.04	53.1	0.278	63.5	0.124	-123.7
1900	0.428	131.5	1.94	50.9	0.292	62.5	0.128	-126.6
2000	0.427	128.4	1.86	49.2	0.306	61.3	0.131	-129.1

f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.392	-125.2	30.12	111.6	0.023	62.6	0.411	-67.0
200	0.380	-153.9	16.44	97.6	0.037	67.6	0.235	-78.0
300	0.379	-167.5	11.03	90.8	0.053	70.8	0.170	-82.6
400	0.380	-175.1	8.33	86.2	0.069	72.1	0.139	-86.5
500	0.381	178.8	6.68	82.5	0.085	72.2	0.121	-89.3
600	0.381	173.2	5.59	79.4	0.100	72.3	0.111	-93.0
700	0.390	168.9	4.82	76.5	0.116	71.7	0.105	-95.3
800	0.389	165.1	4.25	73.5	0.132	71.1	0.102	-98.9
900	0.394	160.4	3.79	71.2	0.148	70.7	0.101	-101.5
1000	0.393	157.7	3.43	68.6	0.163	69.7	0.100	-105.7
1100	0.396	153.6	3.13	66.0	0.178	69.0	0.100	-107.8
1200	0.403	150.0	2.89	63.8	0.193	67.9	0.103	-111.8
1300	0.407	147.4	2.70	61.4	0.209	67.0	0.103	-113.8
1400	0.410	144.0	2.52	59.2	0.223	66.1	0.106	-117.1
1500	0.411	141.2	2.36	57.0	0.238	65.0	0.108	-120.5
1600	0.414	138.5	2.25	54.9	0.253	64.0	0.113	-122.6
1700	0.416	136.4	2.13	52.6	0.267	63.0	0.115	-125.9
1800	0.428	132.5	2.03	50.6	0.281	62.0	0.118	-128.8
1900	0.436	130.7	1.94	48.6	0.295	60.9	0.123	-131.2
2000	0.431	127.3	1.87	46.8	0.309	59.8	0.124	-134.1

### Package Dimensions



### Ordering Information

Part Name	Quantity	Shipping Container
2SC5890FS-TL-E	3000	φ 178 mm Reel, 8 mm Emboss Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

## RENESAS Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Keep safety first in your circuit designs!

1. Renesas Technology Corp. puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

Notes regarding these materials

1. These materials are intended as a reference to assist our customers in the selection of the Renesas Technology Corp. product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Renesas Technology Corp. or a third party.
2. Renesas Technology Corp. assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples contained in these materials.
3. All information contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Renesas Technology Corp. without notice due to product improvements or other reasons. It is therefore recommended that customers contact Renesas Technology Corp. or an authorized Renesas Technology Corp. product distributor for the latest product information before purchasing a product listed herein. The information described here may contain technical inaccuracies or typographical errors. Renesas Technology Corp. assumes no responsibility for any damage, liability, or other loss rising from these inaccuracies or errors. Please also pay attention to information published by Renesas Technology Corp. by various means, including the Renesas Technology Corp. Semiconductor home page (<http://www.renesas.com>).
4. When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products. Renesas Technology Corp. assumes no responsibility for any damage, liability or other loss resulting from the information contained herein.
5. Renesas Technology Corp. semiconductors are not designed or manufactured for use in a device or system that is used under circumstances in which human life is potentially at stake. Please contact Renesas Technology Corp. or an authorized Renesas Technology Corp. product distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.
6. The prior written approval of Renesas Technology Corp. is necessary to reprint or reproduce in whole or in part these materials.
7. If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination. Any diversion or reexport contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited.
8. Please contact Renesas Technology Corp. for further details on these materials or the products contained therein.



### RENESAS SALES OFFICES

<http://www.renesas.com>

Refer to "<http://www.renesas.com/en/network>" for the latest and detailed information.

#### **Renesas Technology America, Inc.**

450 Holger Way, San Jose, CA 95134-1368, U.S.A  
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

#### **Renesas Technology Europe Limited**

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.  
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

#### **Renesas Technology Hong Kong Ltd.**

7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong  
Tel: <852> 2265-6688, Fax: <852> 2730-6071

#### **Renesas Technology Taiwan Co., Ltd.**

10th Floor, No.99, Fushing North Road, Taipei, Taiwan  
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

#### **Renesas Technology (Shanghai) Co., Ltd.**

Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China  
Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

#### **Renesas Technology Singapore Pte. Ltd.**

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632  
Tel: <65> 6213-0200, Fax: <65> 6278-8001

#### **Renesas Technology Korea Co., Ltd.**

Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea  
Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

#### **Renesas Technology Malaysia Sdn. Bhd.**

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia  
Tel: <603> 7955-9390, Fax: <603> 7955-9510